

# **ABSTRACT OF THE DISCLOSURE**

A hermetically coated device includes an integrated semiconductor circuit die, a first layer comprising an inorganic material, the first layer  
5 enveloping the integrated semiconductor circuit die, a second layer, the second layer enveloping the integrated semiconductor circuit die. Formation of such device includes steps of providing an integrated semiconductor circuit die, applying a first layer comprising an  
10 inorganic material, the first layer enveloping the integrated semiconductor circuit die, and applying a second layer, the second layer enveloping the integrated semiconductor circuit die.

2025706 021302